



#### **General Description**

The WST2304 is the highest performance trench N-ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the small power switching and load switch applications.

The WST2304 meet the RoHS and Green Product requirement with full function reliability approved.

#### **Features**

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent Cdv/dt effect decline
- Green Device Available

#### **Product Summery**

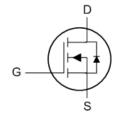
BVDSS	RDSON	ID
20V	20mΩ	6.3A

### **Applications**

- Power management in portable and battery operated products
- One cell battery pack protection
- Load Switch

## **SOT-23N Pin Configuration**





## **Absolute Maximum Ratings**

Symbol	Parameter	Rating	Units	
$V_{DS}$	Drain-Source Voltage	20	V	
$V_{GS}$	Gate-Source Voltage	±8	<b>V</b>	
I <sub>D</sub> @T <sub>c</sub> =25℃	Continuous Drain Current, V <sub>GS</sub> @ 4.5V <sup>1</sup>	6.3	Α	
I <sub>D</sub> @T <sub>c</sub> =70°C	Continuous Drain Current, V <sub>GS</sub> @ 4.5V <sup>1</sup>	5.0	Α	
I <sub>DM</sub>	Pulsed Drain Current <sup>2</sup>	22	Α	
P <sub>D</sub> @T <sub>A</sub> =25℃	Total Power Dissipation <sup>3</sup>	1.0	W	
T <sub>STG</sub>	Storage Temperature Range -55 to 150		$^{\circ}$	
$T_J$	Operating Junction Temperature Range -55 to 150		$^{\circ}$ C	

#### **Thermal Data**

Symbol	Parameter	Тур.	Max.	Unit
$R_{ heta JA}$	Thermal Resistance Junction-ambient <sup>1</sup>		110	°C/W
$R_{ heta JC}$	Thermal Resistance Junction-Case <sup>1</sup>		70	°C/W



**N-Ch MOSFET** 

# Electrical Characteristics (T<sub>J</sub>=25 C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =250uA	20			V
$\triangle BV_{DSS}/\triangle T_{J}$	BVDSS Temperature Coefficient	Reference to 25°C , I <sub>D</sub> =1mA		0.028		V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =4.5V , I <sub>D</sub> =4A		20	25	mΩ
		V <sub>GS</sub> =2.5V , I <sub>D</sub> =3A		24	35	
		V <sub>GS</sub> =1.8V , I <sub>D</sub> =2A		32	44	
V <sub>GS(th)</sub>	Gate Threshold Voltage	\/ -\/   -250uA	0.3	0.7	1.0	V
$\triangle V_{GS(th)}$	V <sub>GS(th)</sub> Temperature Coefficient	$V_{GS}=V_{DS}$ , $I_D=250uA$		-3.21		mV/℃
	Drain-Source Leakage Current	$V_{DS}$ =16V , $V_{GS}$ =0V , $T_{J}$ =25 $^{\circ}\mathrm{C}$			1	uA
I <sub>DSS</sub>		$V_{DS}$ =16V , $V_{GS}$ =0V , $T_J$ =55 $^{\circ}\mathrm{C}$			5	uA
I <sub>GSS</sub>	Gate-Source Leakage Current	$V_{GS}=\pm12V$ , $V_{DS}$ =0V			±100	nA
gfs	Forward Transconductance	V <sub>DS</sub> =5V , I <sub>D</sub> =5A		24		S
$R_g$	Gate Resistance	V <sub>DS</sub> =0V , V <sub>GS</sub> =0V , f=1MHz		1.8	4.2	Ω
Qg	Total Gate Charge (4.5V)			8.5	13	
Q <sub>gs</sub>	Gate-Source Charge	V <sub>DS</sub> =15V , V <sub>GS</sub> =4.5V , I <sub>D</sub> =5A		1.56	2.5	nC
$Q_gd$	Gate-Drain Charge			2.6	4.7	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}$ =10V , $V_{GS}$ =10V , $R_{G}$ =3.3 $\Omega$		6.0	8.7	
T <sub>r</sub>	Rise Time			27	50	ns
$T_{d(off)}$	Turn-Off Delay Time			23	38	
T <sub>f</sub>	Fall Time			8.5	17.1	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =15V , V <sub>GS</sub> =0V , f=1MHz		574		
C <sub>oss</sub>	Output Capacitance			67		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			60		

#### **Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
I <sub>S</sub>	Continuous Source Current <sup>1,4</sup>	V =V =0V Force Current			2.8	Α
I <sub>SM</sub>	Pulsed Source Current <sup>2,4</sup>	V <sub>G</sub> =V <sub>D</sub> =0V , Force Current			22	Α
$V_{SD}$	Diode Forward Voltage <sup>2</sup>	$V_{GS}$ =0V , $I_S$ =1A , $T_J$ =25 $^{\circ}$ C			1.2	V
t <sub>rr</sub>	Reverse Recovery Time			10.2		nS
Q <sub>rr</sub>	Reverse Recovery Charge	IF=5A , dI/dt=100A/ $\mu$ s , T $_{J}$ =25 $^{\circ}$ C		2.9		nC

#### Note:

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper,t<10sec.
- 2.The data tested by pulsed , pulse width  $\,\leq\,300\text{us}$  , duty cycle  $\,\leq\,2\%$
- 4. The data is theoretically the same as  $I_D$  and  $I_{DM}$ , in real applications, should be limited by total power dissipation.



**N-Ch MOSFET** 

## **Typical Characteristics**

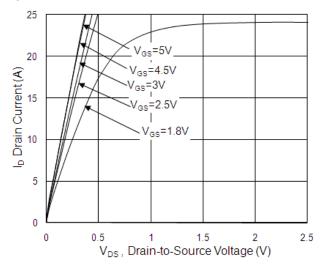


Fig.1 Typical Output Characteristics

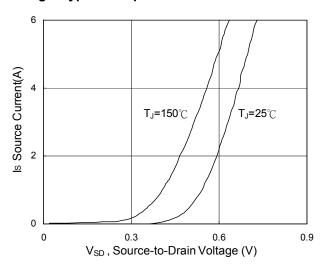


Fig.3 Forward Characteristics of reverse

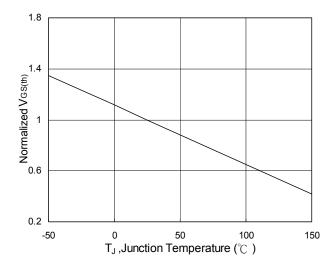


Fig.5  $V_{GS(th)}$  vs.  $T_J$ 

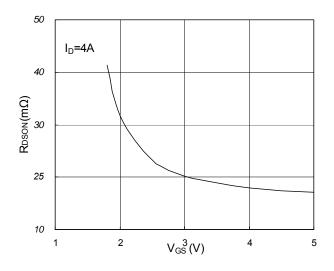


Fig.2 On-Resistance vs. Gate-Source

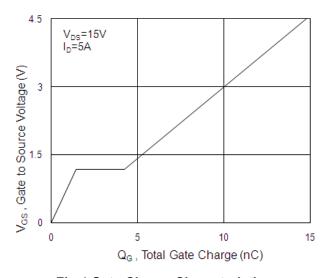


Fig.4 Gate-Charge Characteristics

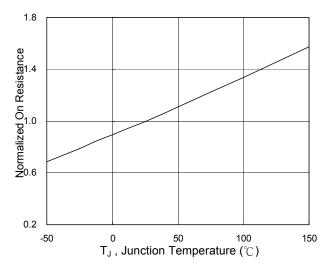
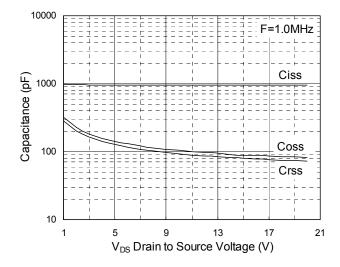


Fig.6 Normalized R<sub>DSON</sub> vs. T<sub>J</sub>







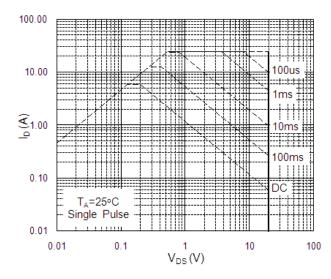


Fig.7 Capacitance

Fig.8 Safe Operating Area

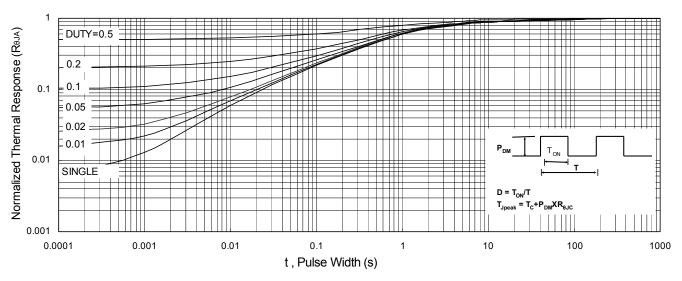


Fig.9 Normalized Maximum Transient Thermal Impedance

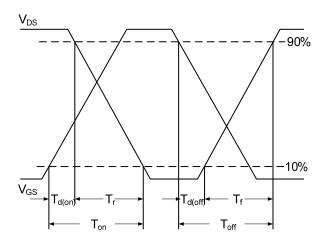


Fig.10 Switching Time Waveform

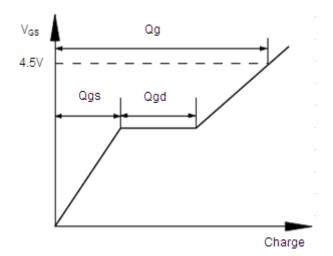


Fig.11 Gate Charge Waveform



#### **Attention**

- 1, Any and all Winsok power products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your Winsok power representative nearest you before using any Winsok power products described or contained herein in such applications.
- 2, Winsok power assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all Winsok power products described or contained herein.
- 3, Specifications of any and all Winsok power products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.
- 4, Winsok power Semiconductor CO., LTD. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.
- 5,In the event that any or all Winsok power products (including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.
- 6, No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of Winsok power Semiconductor CO., LTD.
- 7, Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. Winsok power believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.
- 8, Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the Winsok power product that you Intend to use.
- 9, this catalog provides information as of Sep.2014. Specifications and information herein are subject to change without notice.